

25G GaAs PD 1x4 Array

PD0850G025-A04-003

Preliminary



Feature

- 40um optical detection mesa area.
- Top-side illuminated device.
- AR coating for wide wavelength range.
- High cut-off frequency.
- Low dark current and capacitance..

Device Electro-Optical Characteristics

All parameters for T = 25°C unless otherwise noted.

PARAMETER	SYMBOL	UNIT	MIN.	TYP.	MAX.	TEST CONDITIONS
Breakdown Voltage	Vbr	V	30			Id=-1uA
Dark Current	Id	nA		0.2	1	V=-5V
Capacitance	C	pF		0.15	0.17	V=-5V, f=1MHz
Responsivity	R	A/W	0.5			λ=850nm
Overload	Po	dBm	0			λ=850nm
Bandwidth	3dB	GHz		20		V=-2V

Device Physical Specifications 1X4 Array

PARAMETER	UNIT	MIN.	TYP.	MAX.
Bond Pad	um		70*70	
Chip size	um		250X1000	
Chip Hight	um		150	

Absolute Maximum Ratings

PARAMETER	SYMBOL	UNIT	Ratings
Forward Current	If	mA	5
Reverse Voltage	Vr	V	20
Operating Temperature	To	°C	-40 to +85
Storage Temperature	Tst	°C	-40 to +100
Incident Optical power	Pm	dBm	+3dBm

CoreOptics reserves the right to make changes due to the improvement of process technology.